

subjecting the ion traces of the first and second plurality to a chemical etching process for forming recesses extending from the surface to within the carrier material at an aspect ratio of A from about ≥ 3 to about 4 and whereby two or more of such recesses intersect below the surface to form common chambers.

Please amend claim 22 is follows:

22. (Currently amended) The method of claim 21, further including the ~~steps~~ step of blocking at least part of the at least one beam ~~and of selectively decelerating the ions.~~

39. (Currently amended) A system for processing a surface of a dielectric carrier material to adapt it for securely attaching thereto a cover layer by precipitation, comprising:

means for placing the dielectric carrier material in a predetermined position;

means for generating at least one beam of high energy heavy ions along a predetermined path;

means for directing the ions into the carrier material through one surface thereof to form intersecting latent ion traces therein any at least two of which being ~~daped~~ adapted to be etched into a common volume;

means mounted between the source and the dielectric carrier material for selectively blocking at least a portion of the beam; and

means mounted between the source and the means for blocking for selectively decelerating the ions.

Remarks.

The changes to the specification are reflected, with amendatory markings, in one version of a substitute specification and, without such markings, in another version of a substitute specification. This form of amendment, because of the newly introduced section headings, is thought to be more convenient to the Examiner than would be amended paragraphs shown